

0976559.00001

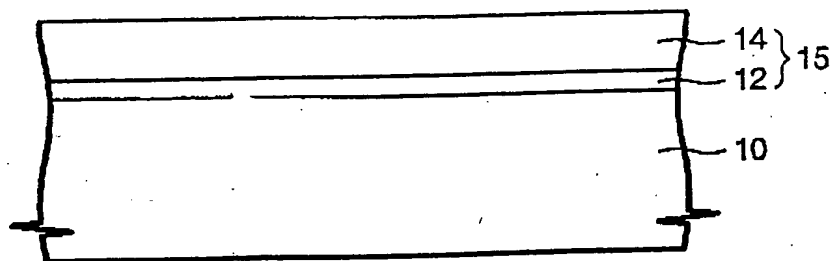


Fig. 1A

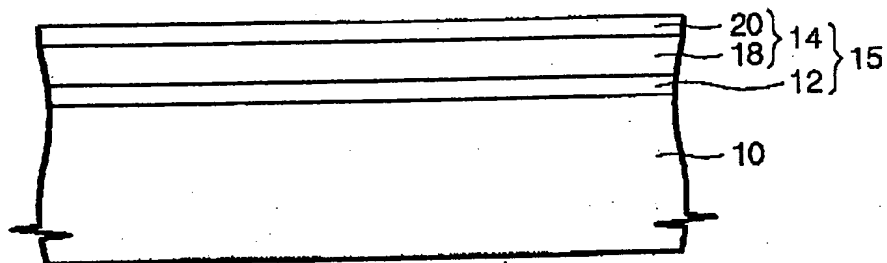


Fig. 1B

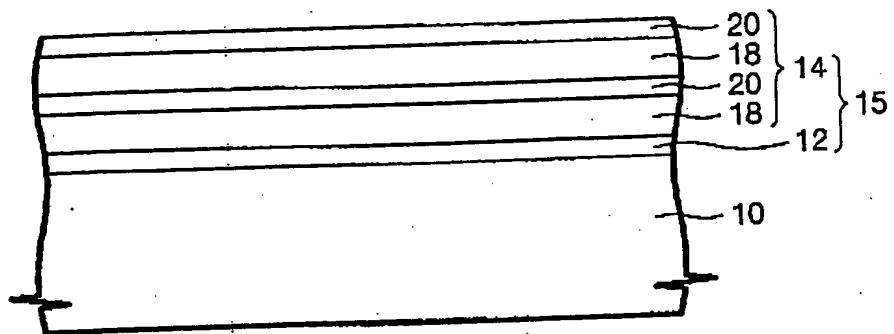


Fig. 1C

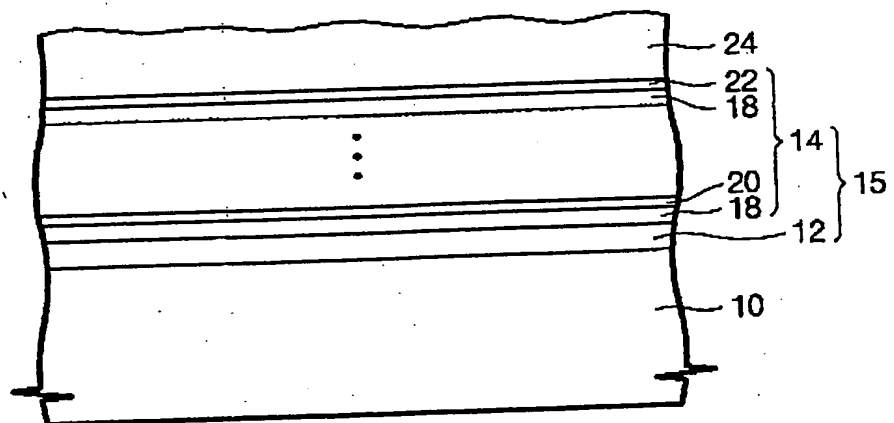
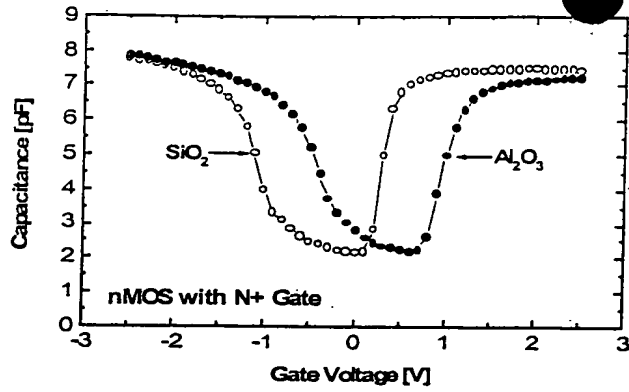
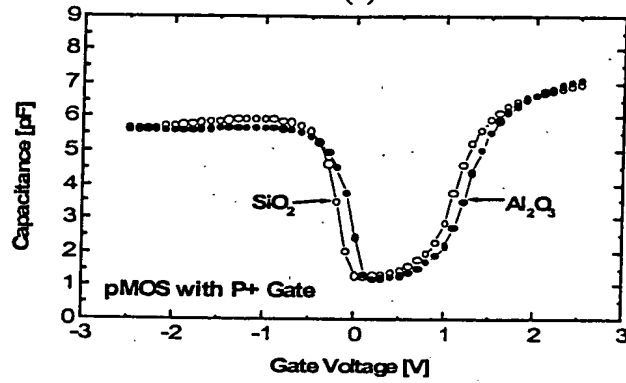


Fig. 2

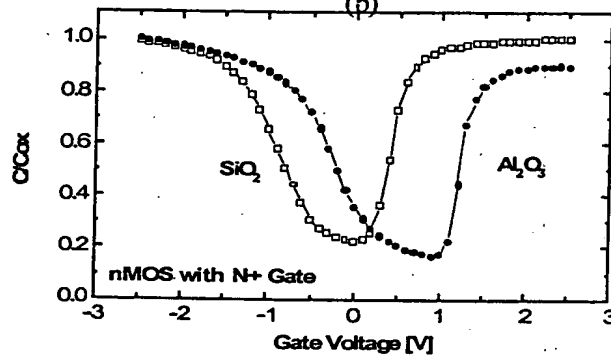
T02020" 6099/150



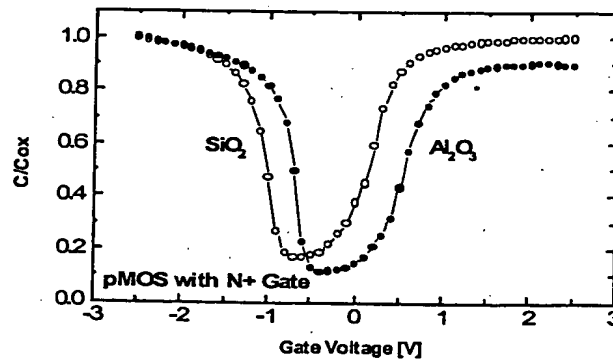
(a)



(b)



(c)



(d)

### Al<sub>2</sub>O<sub>3</sub> MOS Capacitor C-V Curves

(a) n+Poly-Si/ Al<sub>2</sub>O<sub>3</sub> or SiO<sub>2</sub>/ p-Si (b) p+Poly-Si/  
Al<sub>2</sub>O<sub>3</sub> or SiO<sub>2</sub>/ n-Si (c) n+Poly-Si/ Al<sub>2</sub>O<sub>3</sub> or  
SiO<sub>2</sub>/ p-Si (d) n+Poly-Si/ Al<sub>2</sub>O<sub>3</sub> or SiO<sub>2</sub>/ n-Si

FIG. 3

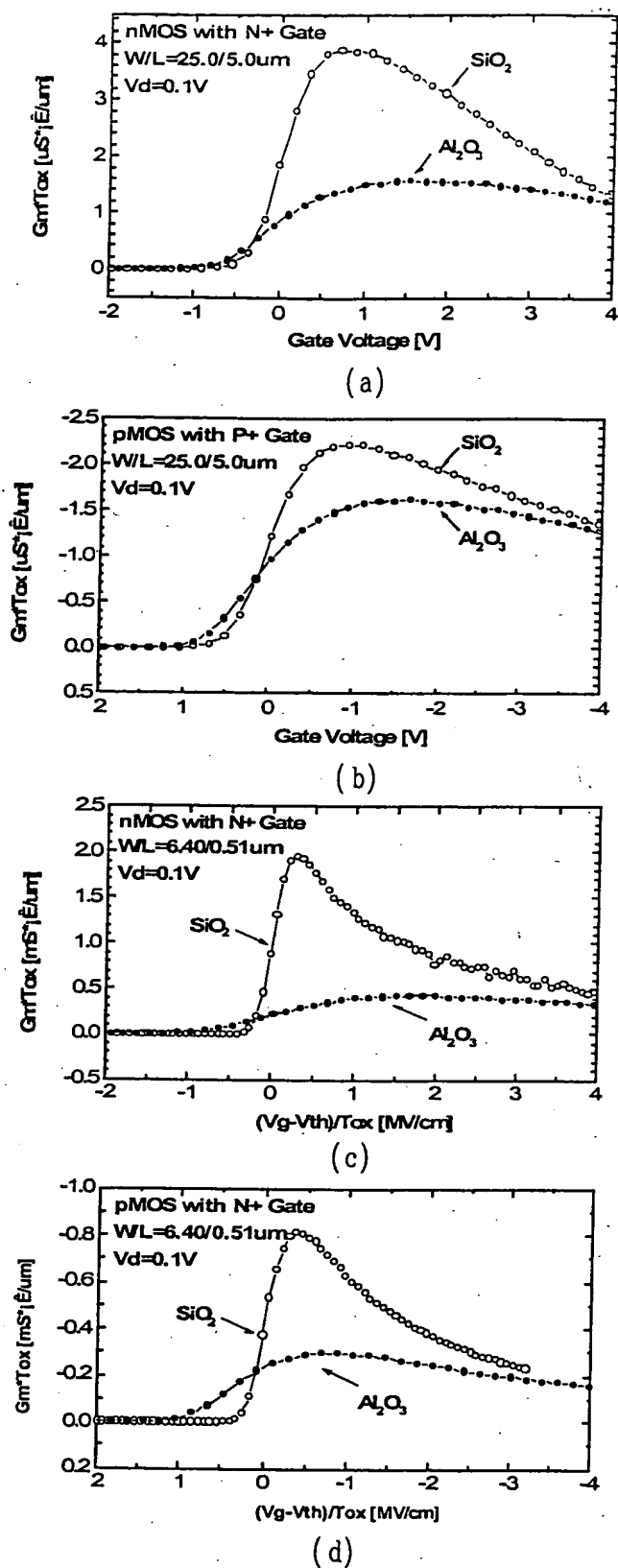
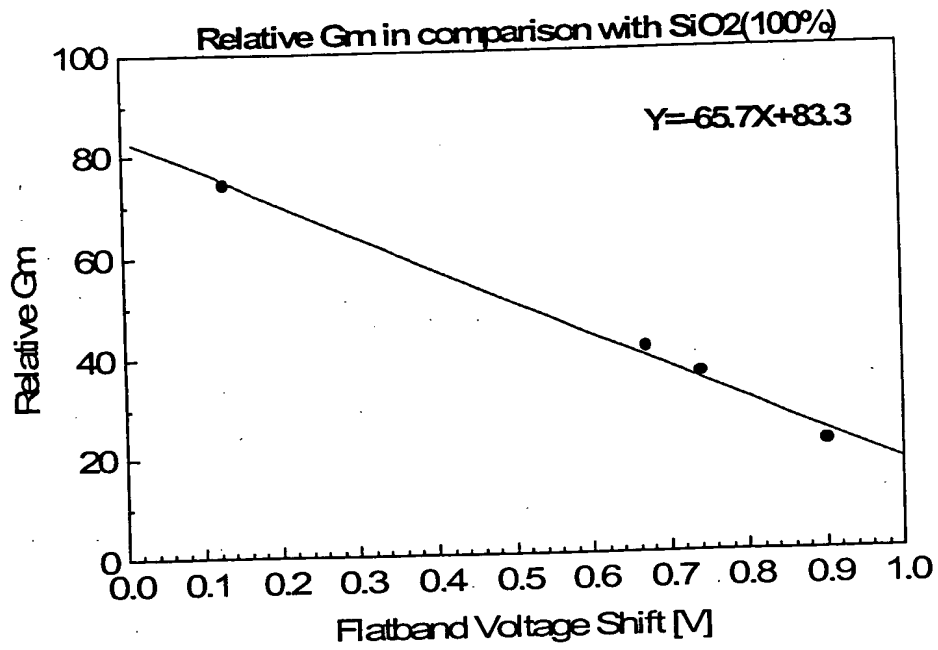


FIG. 4

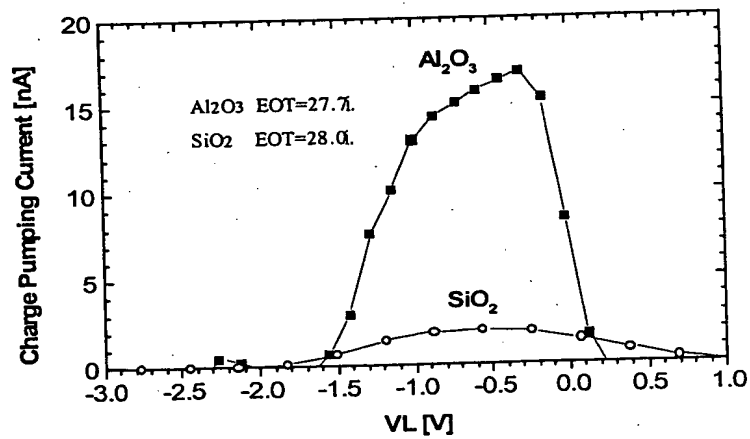
- $G_m(\text{Normalized Transconductance})$  vs.  $V_g$
- (a) N+Gate nMOS (b) P+Gate pMOS
  - (c) In-situ Doped N+Gate nMOS
  - (d) In-situ Doped N+Gate pMOS

T02030" 65094750



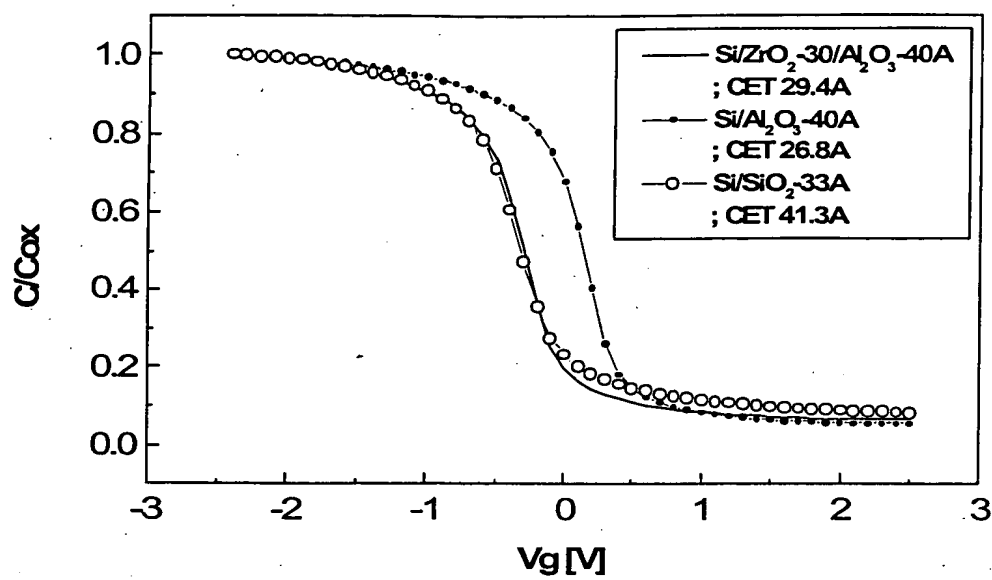
Flatband Voltage Shift vs. Relative Gm of Al<sub>2</sub>O<sub>3</sub> to SiO<sub>2</sub>

FIG. 5



Gate Base Level VL vs. Charge Pumping Current I<sub>cp</sub>

FIG. 6



C-V Curve of ZrO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> Stack layer

FIG. 7